

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

A. Interconnect & Package 분과

Room A
태백 I (5층)

2016년 2월 24일(수) 08:30-10:00

[WA1-A] A1: Contact and Thin Film Technologies for High Performance Interconnect

좌장 : 이원준(세종대학교)

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| WA1-A-1 | 08:30-08:45 | Self-limiting Growth with High Throughput of Thin Film Deposition by Pulsed PE-CVD
Hanearl Jung and Hyungjun Kim
<i>School of Electrical and Electronic Engineering, Yonsei University</i> |
| WA1-A-2 | 08:45-09:00 | The Effects on The Microstructure Evolution and Electrical Properties of Yb Alloyed with Mo for Silcication
Sekwon Na ¹ , Seok-Hee Lee ² , Hoo-Jeong Lee ³ , and Young-Chang Joo ^{1,4}
<i>¹Research Institute of Advanced Materials, Seoul National University, ²Department of Electrical Engineering, KAIST, ³School of Advanced Materials Science and Engineering, Sungkyunkwan University, ⁴Department of Materials Science and Engineering, Seoul National University</i> |
| WA1-A-3 | 09:00-09:15 | WC_x Thin Films Prepared by Atomic Layer Deposition as A Metal Gate and Diffusion Barrier for Cu Metallization
Jun Beom Kim ¹ , Won Seok Han ² , Tae Eun Hong ³ , and Soo-Hyun Kim ¹
<i>¹School of Materials Science and Engineering, Yeungnam University, ²UP Chemical, ³Busan Center, Korea Basic Science Institute</i> |
| WA1-A-4 | 09:15-09:30 | Consideration for Effective NMOS Contact Resistivity Reduction Via INDA(Interface N-type Dopant Accumulation) Using TiSi₂ with Titanium/Selenium Double Layer on in-Situ Doped Si:P Film.
Jeongmin Choi, Enjung Ko, Mijin Jung, Seran Park, Hyunsu Shin, and Dae-Hong Ko
<i>Department of Materials Science and Engineering, Yonsei University</i> |
| WA1-A-5 | 09:30-09:45 | Atomic Layer Deposition of Ru Thin Films using A New Ru Precursor and Various Reactants for A Cu Seed Layer Application
Hyun-Jung Lee ¹ , Min-Young Lee, Soon-Young Jung, Tae Eun Hong ² , Ryosuke Harada ³ , Shunichi Nabeya ⁴ , and Soo-Hyun Kim ¹
<i>¹School of Materials Science and Engineering, Yeungnam University, ²Busan Center, Korea Basic Science Institute, ⁴Tanaka Precious Metals, Japan</i> |